

Title (en)
SEMICONDUCTOR DEVICE WITH A ROUGHENED SEMICONDUCTIVE SURFACE

Title (de)
HALBLEITERVORRICHTUNG MIT AUFGERAUHTER HALBLEITEROBERFLÄCHE

Title (fr)
DISPOSITIF SEMI-CONDUCTEUR A SURFACE SEMI-CONDUCTRICE RUGUEUSE

Publication
EP 0811250 A1 19971210 (DE)

Application
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Abstract (en)
[origin: DE19506323A1] A semiconductor device has a semiconductor body of which at least part of the non metallised contact surface is roughened. The metallised contact layer is made of a base metallic material such as aluminium. A process that does not attack the metallised contact surface is used to roughen the semiconductive surface.

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Citation (search report)
See references of WO 9626550A1

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